NEC

NPN SILICON TRANSISTOR 2SC1941

DESCRIPTION

The 2SC1941 is designed for use in driver stages of audio

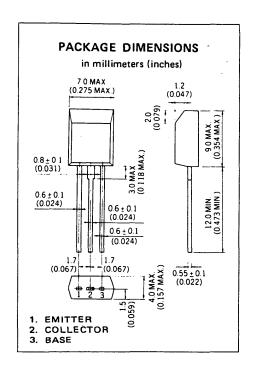
frequency amplifiers.

FEATURES

- High total power dissipation and high breakdown voltage:
 1.0 W at 25 °C ambient temperature/V_{CFO}=160 V
- Complementary to the NEC 2SA916 PNP transistor.

ABSOLUTE MAXIMUM RATINGS

Maximum Te	mperatures							
Storage Temperature –55 to +150 °C								
Junction Temperature +150 °C Maximur								
Maximum Po	wer Dissipation (Ta = $25 ^{\circ}$ C)							
Total Power Dissipation								
Thermal Resistance(junction to Ambient)125 °C/W								
Maximum Vo	Itages and Currents (Ta = 25 °C)							
V _{CBO}	Collector to Base Voltage	160	٧					
V _{CEO}	Collector to Emitter Voltage	160	٧					
V _{EBO}	Emitter to Base Voltage	5.0	٧					
Ic	Collector Current	50 n	nΑ					
I _B	Base Current	10 n	nΑ					



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1	DC Current Gain	90	200	400	_	V _{CE} = 10 V, I _C =10 mA
hFE2	DC Current Gain	50	180		· -	V _{CE} = 10 V, I _C =1.0 mA
f⊤	Gain Bandwidth Product	50	120		MHz	V _{CE} = 10 V, I _E =-10 mA
c _{ob}	Output Capacitance		2.3	3.0	pF	V _{CB} = 10 V, I _E =0, f=1.0 MHz
СВО	Collector Cutoff Current			100	nA	V _{CB} = 160 V, I _E =0
^I EBO	Emitter Cutoff Current			100	nA -	V _{EB} = 5.0 V, I _C =0
VBE	Base to Emitter Voltage	650	685	750	mV	V _{CE} = 10 V, I _C =10 mA
V _{CE(sat)}	Collector Saturation Voltage		0.07	0.6	V	I _C = 20 mA, I _B =2.0 mA
V _{BE (sat)}	Base Saturation Voltage		0.75	1.0	V	I _C = 20 mA, I _B =2.0 mA

Classification of hFE1

Rank	М	L	κ	
Range	90 180	135 – 270	200 – 400	

 h_{E1} Test Conditions: $V_{CE} = 10 \text{ V}$, $I_{C} = 10 \text{ mA}$

TYPICAL CHARACTERISTICS (Ta=25 °C unless otherwise noted)

